

Abstracts

High-Performance and High-Yield Ka-Band Low-Noise MMIC Using 0.25- μ m Ion-Implanted MESFET's

J. Mondal, J. Detry, J. Geddes and D.C. Geddes. "High-Performance and High-Yield Ka-Band Low-Noise MMIC Using 0.25- μ m Ion-Implanted MESFET's." 1991 Microwave and Guided Wave Letters 1.7 (Jul. 1991 [MGWL]): 167-169.

Three-stage low-noise amplifiers fabricated using high-yield 0.25- μ m ion-implanted process showed 4.2 dB average noise figure with a 15-dB gain in Ka-band.

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